

HF/VHF/UHF RF power N-channel MOSFETs

Datasheet - production data

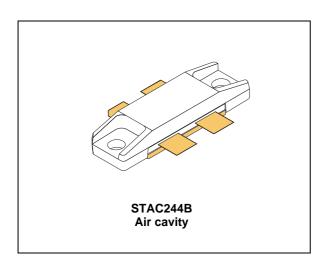
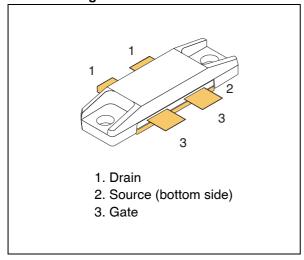


Figure 1. Pin connection



Features

- · Gold metallization
- Excellent thermal stability
- Common source push-pull configuration
- P_{OUT} = 300 W min. with 20 dB gain @ 175 MHz
- In compliance with the 2002/95/EC European directive
- ST air cavity packaging technology STAC[™] package

Description

The STAC2932B is a gold metallized N-channel MOS field-effect RF power transistor, intended for use in 50 V DC large signal applications up to 250 MHz.

The STAC2932B benefits from the latest generation of efficient, patent-pending package technology, otherwise known as STAC[™].

Table 1. Device summary

Order code	Marking	Base qty.	Package	Packaging
STAC2932BW	STAC2932 ⁽¹⁾	20	STAC244B	Tray

^{1.} For more details please refer to Chapter 7: Marking, packing and shipping specifications.

Contents STAC2932B

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STAC2932B Electrical data

1 Electrical data

1.1 Maximum ratings

 $(T_{CASE} = 25 \, ^{\circ}C)$

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{(BR)DSS} ⁽¹⁾	Drain source voltage	125	V
V _{DGR}	Drain-gate voltage ($R_{GS} = 1 M\Omega$)	125	V
V _{GS}	Gate-source voltage	±20	V
I _D	Drain current	40	Α
P _{DISS}	Power dissipation	625	W
TJ	Max. operating junction temperature	200	°C
T _{STG}	Storage temperature	-65 to +150	°C

^{1.} $T_J = 150$ °C

1.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Junction - case thermal resistance	0.28	°C/W

Electrical characteristics STAC2932B

2 Electrical characteristics

 $T_{CASE} = +25 \, ^{\circ}C$

2.1 Static

Table 4. Static (per side)

Symbol		Test conditions			Тур.	Max.	Unit
V _{(BR)DSS}	$V_{GS} = 0 V$	$I_{DS} = 100 \text{ mA}$		125			V
I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 50 \text{ V}$				50	μΑ
IGSS	V _{GS} = 20 V	$V_{DS} = 0 V$				250	nA
V _{GS(Q)}	V _{DS} = 10 V	$I_D = 250 \text{ mA}$		1.5	2.5	4.0	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 10 A				3.0	٧
G _{FS}	V _{DS} = 10 V	I _D = 5 A		5			S
C _{ISS}					468		pF
C _{OSS}	V _{GS} = 0 V	$V_{DS} = 50 \text{ V}$	f = 1 MHz		206		pF
CRSS					16		pF

2.2 Dynamic

Table 5. Dynamic

Symbol	Test conditions		Тур.	Max.	Unit
P _{OUT}	V _{DD} = 50 V, I _{DQ} = 2 x 250 mA, P _{IN} = 4 W, f = 175 MHz	300	390		W
h _D	V _{DD} = 50 V, I _{DQ} = 2 x 250 mA, P _{IN} = 4 W, f = 175 MHz	55	68		%

STAC2932B Impedance

3 Impedance

Figure 2. Current conventions

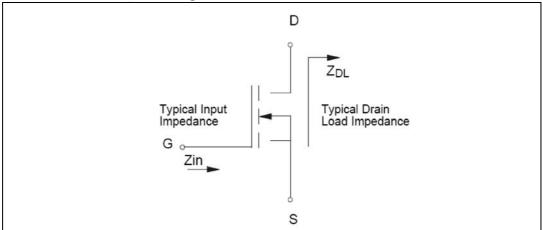


Table 6. Impedance data

Freq. (MHz)	Z _{IN} (Ω)	Z _{DL} (Ω)	
175 MHz	2.0 - j2.0	3.5 + j5.2	

Note: Measured gate to gate and drain to drain, respectively.

Typical performance STAC2932B

4 Typical performance

Figure 3. Capacitances vs drain supply voltage Figure 4. Output power vs drain supply voltage

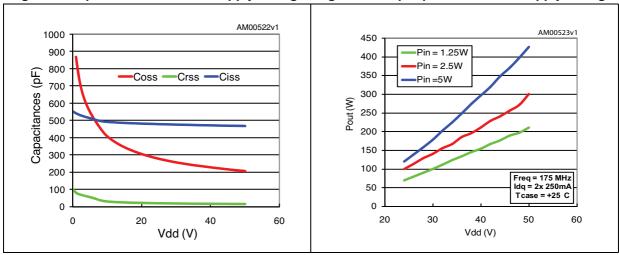
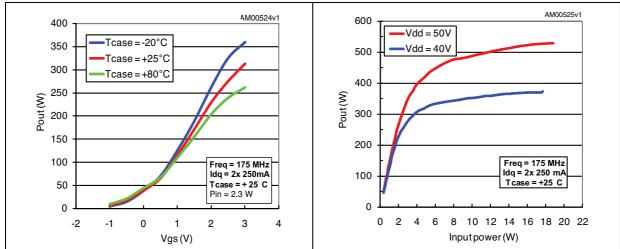


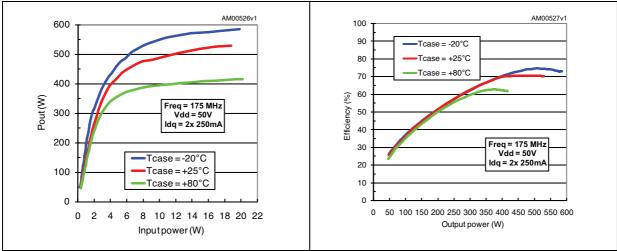
Figure 5. Output power vs gate voltage





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Figure 7. Output power vs input power and case temperature Figure 8. Efficiency vs output power and case temperature



Test circuit STAC2932B

5 Test circuit

DIMENSION TABLE -0.056" SPACE TRANSMISSION LINE DIMENSIONS FB6 50V C25 +Vgg C15 C21 FB1 C5 C11 C10 T2 SORE C16 FB2 ____C14 R5 FB4 ~~~~ C22 C20 C24 1. DIMENSIONS AT COMPONENT SYMBOLS ARE REFERENCE FOR COMPONENT PLACEMENT. SEE SHEET 1. 2. GAP BETWEEN GROUND & TRANSMISSION LINES IS 0.056[1.42]

Figure 9. 175 MHz test circuit schematic (production test circuit)

Table 7. 175 MHz test circuit part list

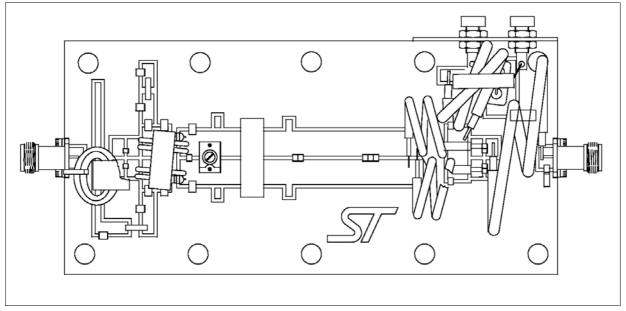
Component	Description	
C1, C2, C14, C15, C24, C25	1200 pF ATC 700B chip capacitor	
C5	75 pF ATC 100B chip capacitor	
C6	ST406 variable capacitor	
C9, C10	47 pF ATC 100B chip capacitor	
C11, C12, C13	43 pF ATC 100B chip capacitor	
C16, C18	470 pF ATC 100B chip capacitor	
C17, C19, C20, C21	10,000 pF ATC 200B chip capacitor	
C22, C23	0.1 μF 200 V chip capacitor	
C28	10 μF 100 V electrolytic capacitor	
C29	0.8 - 8 pF variable capacitor	
R1, R2, R5, R6	430 Ω, 1/2 W chip resistor	

STAC2932B Test circuit

Table 7. 175 MHz test circuit part list (continued)

Component Description		
R3, R4	270 Ω 1/2 W axial lead resistor	
B1	RG-316 50 Ω 11.8" thru ferrite toroidal	
B2	RG-142 50 Ω 11.8"	
T1	4:1, RG-316 25 Ω, 5.9", 2 turns thru ferrite core	
T2	1:4, 25 Ω semi-rigid cable, OD.141", 5.9"	
L1	λ /4 inductor, RG-142 50 Ω , 11.8", 3 turns thru ferrite toroid	
FB1,FB5	Ferrite toroidal	
FB2, FB6	Multi-aperture core	
FB3, FB4 Surface mount ferrite bead		
PCB	Rogers ultralam 2000, Er 2.55, 0.060"	

Figure 10. Circuit layout



6 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

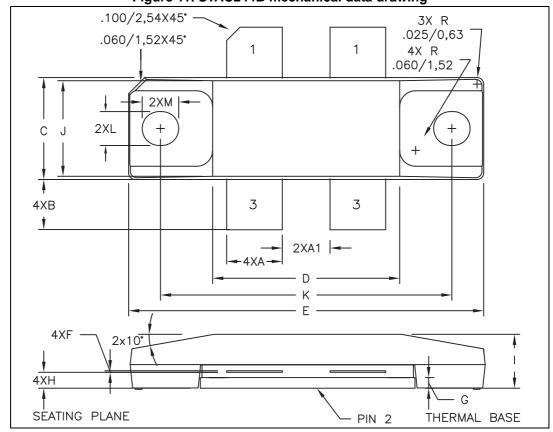


Figure 11. STAC244B mechanical data drawing

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Table 8. STAC244B mechanical data

Disc		mm				
Dim.	Min.	Тур.	Max.			
Α	5.08		5.59			
A1	4.32		4.83			
В	4.32		5.33			
С	9.65		9.91			
D	17.78		18.08			
E	33.88		34.19			
F	0.10		0.15			
G		1.02				
Н	1.45		1.70			
I	4.83		5.33			
J	9.27		9.52			
К	27.69		28.19			
L	3.12	3.23	3.33			
М	3.35	3.45	3.56			



7 Marking, packing and shipping specifications

Table 9. Packing and shipping specifications

Order code	Packaging	Pcs per tray	Dry pack humidity	Lot code
STAC2932BW	Tray	20	< 10 %	Not mixed

Figure 12. Marking layout

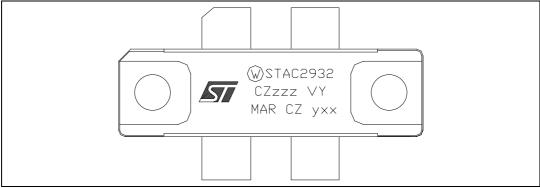


Table 10. Marking specifications

Symbol Description		
W	Wafer process code	
CZ	Assembly plant	
xxx	Last 3 digit of diffusion lot	
VY	Diffusion plant	
MAR	Country of origin	
CZ	Test and finishing plant	
у	Assembly year	
уу	Assembly week	

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STAC2932B Revision history

8 Revision history

Table 11. Document revision history

Date	Revision	Changes
20-Mar-2009	1	First release.
29-Jun-2010	2	Updated features and description on cover page.
12-Aug-2011	3	Update figures on coverpage and Section 6: Package mechanical data. Inserted Section 7: Marking, packing and shipping specifications. Minor text changes.
05-Sep-2011	4	Update L and M dimensions <i>Table 8 on page 11</i> .
12-Jan-2012	5	Minor text changes to improve readability.
27-Jan-2014	6	Modified pin labeling in Figure 1: Pin connection.

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